

PNP Transistors

6501130 NATL SEMICOND, (DISCRETE)

28C 35437  
T-37-01 D

Type No.	Case Style	V <sub>CB0</sub> (V) Min	V <sub>CE0</sub> (V) Min	V <sub>EB0</sub> (V) Min	I <sub>CB0</sub> (mA) Max	V <sub>CB</sub> (V)	h <sub>FE</sub> Min	I <sub>C</sub> (mA) Max	V <sub>CE</sub> (V)	V <sub>BE(SAT)</sub> (V) & V <sub>BE(SAT)</sub> (V) @ I <sub>C</sub> (mA)		C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	I <sub>C</sub> (mA) Max	t <sub>off</sub> (ns) Max	NF (dB) Max	Test Conditions	Process No.
										Max	Min							
2N869	TO-52	25		5	10	15	20	120	5	1.0	1.0	9	100	10				64
2N869A	TO-52	25	18	5	10	15	25	100	1	0.15	0.78	6	400	10	80		1	64
2N995	TO-52	20	15	4	5	15	35	140	1	0.2	0.85	10	100	10				64
2N995A	TO-52	20	15	4	5	15	25	100	1	0.2	0.95	6	100	10	90		2	64
2N2894	TO-52	12	12	4	10*	6	25	100	1	0.15	0.78	6	400	30	90		2	64
2N2894A	TO-52	12	12	4.5	50*	10	30	100	1	0.13	0.78	4.5	800	30	25		3	64
2N3012	TO-52	12	12	4	80*	6	20	100	1	0.15	0.78	6	400	30	75		2	64
2N3209	TO-52	20	20	4	80*	10	15	100	1	0.15	0.78	5	400	30	90		2	64
2N3248	TO-52	15	12	5			20	10	3	0.6	1.7	8	250	20	100		5	64
2N3249	TO-52	15	12	5			35	100	1	0.125	0.6	8	300	20	100		5	64
2N3545	TO-52	20	20	5	10	10	30	100	1	0.2	0.6	8	250	10	90		8	64

SATURATED SWITCHES

6501130 NATL SEMICOND, (DISCRETE)

28C 35438



SATURATED SWITCHES (Continued)

Type No.	Case Style	VCBO (V) Min	VCEO (V) Min	VEBO (V) Min	ICES* ICBO @ VCB (mA) Max	hFE @ IC (mA)		VCE & VCE (V)	VCE(SAT) (V) & VBE(SAT) (V) @ IC (mA)		Cob (pF) Max	ft (MHz)		Ic (mA)	toff (ns) Max	NF (dB) Max	Test Conditions	Process No.	
						Min	Max		Min	Max		Min	Max						Min
2N3546	TO-52	15	12	4.5	10	15	100	1	0.15	0.7	6	700	10	30			9	64	
2N3576	TO-52	20	15	5	10	40	120	1	0.25	0.8		400	10	50			5	64	
2N5056	TO-52	15	15	4.5	50*	30	100	0.5	0.13	0.72	4.5	600	30	35			3	64	
2N5057	TO-52	15	15	4.5	50*	20	100	0.3	0.19	0.8	4.5	800	30	35			3	64	
2N3304	TO-52	6	6	4	10*	30	50	1	0.15	0.7	3.5	500	10	60			7	65	
2N3451	TO-52	6	6	4	10*	15	120	0.3	0.16	0.8	5.5	500	10	60			7	65	
2N3639	TO-92 (92)	Same as PN3639, see page 2-4 for explanation																	
2N3640	TO-92 (92)	Same as PN3640, see page 2-4 for explanation																	
2N4208	TO-52	12	12	4.5	10*	30	50	1	0.13	0.8	3	700	10	20			5	65	
2N4209	TO-52	15	15	4.5	10*	40	50	1	0.15	0.8	3	850	10	20			5	65	
2N4258	TO-92 (92)	Same as PN4258, see page 2-4 for explanation																	
2N4258A	TO-92 (92)	Same as PN4258A, see page 2-4 for explanation																	
2N5140	TO-92 (92)	Same as PN5140, see page 2-4 for explanation																	

T-37-01

TEST CONDITIONS:  
 (1) IC = 30 mA, VCC = 3V, IB<sup>1</sup> = 3 mA, IB<sup>2</sup> = 1.5 mA. (2) IC = 30 mA, VCC = 3V, IB<sup>1</sup> = IB<sup>2</sup> = 1.5 mA. (3) IC = 30 mA, VCC = 3V, IB<sup>1</sup> = IB<sup>2</sup> = 3 mA. (4) IC = 500 mA, VCC = 30V, IB<sup>1</sup> = IB<sup>2</sup> = 50 mA  
 (5) IC = 10 mA, VCC = 3V, IB<sup>1</sup> = IB<sup>2</sup> = 1 mA. (6) IC = 10 mA, VCC = 1.5V, IB<sup>1</sup> = IB<sup>2</sup> = 1 mA. (7) IC = 10 mA, VCC = 1.5V, IB<sup>1</sup> = IB<sup>2</sup> = 500 μA. (8) IC = 10 mA, VCC = 2V, IB<sup>1</sup> = IB<sup>2</sup> = 1 mA. (9) IC = 50 mA  
 VCC = 3V, IB<sup>1</sup> = IB<sup>2</sup> = 5 mA. (10) IC = 1A, VCC = 30V, IB<sup>1</sup> = IB<sup>2</sup> = 100 mA.

PNP Transistors

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**PNP Transistors**

6501130 NATL SEMICOND, (DISCRETE)

28C 35439  
T-37-01 D

**SATURATED SWITCHES (Continued)**

Type No.	Case Style	V <sub>CB0</sub> (V) Min	V <sub>CEO</sub> (V) Min	V <sub>EB0</sub> (V) Min	I <sub>CS0</sub> * (mA) Max	V <sub>CB</sub> (V) Max	I <sub>CE</sub> (mA) Min	I <sub>CE</sub> (mA) Max	V <sub>CE</sub> (V) Min	V <sub>CE</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Min	V <sub>BE(SAT)</sub> (V) Max	I <sub>C</sub> (mA) Min	I <sub>C</sub> (mA) Max	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	f <sub>T</sub> (MHz) Max	I <sub>C</sub> (mA) Min	I <sub>C</sub> (mA) Max	t <sub>off</sub> (ns) Max	NF (dB) Max	Test Conditions	Process No.
2N5771	TO-92 (92)	15	15	4.5	10	8	40	50	1.0	0.3	0.15	0.8	1	10	3	850	10	20		6		65	
2N5910	TO-92 (92)	Same as PN5910, see below for explanation																					
MPS3639	TO-92 (92)	Same as PN3639, see below for explanation																					
MPS3640	TO-92 (92)	Same as PN3640, see below for explanation																					
PN3639	TO-92 (92)	6	6	4	10*	3	20	50	1.0	0.3	0.16	0.8	10	10	3.5	300	10	60		7		65	
PN3640	TO-92 (92)	12	12	4	10*	6	20	50	1.0	0.3	0.2	0.8	10	10	3.5	300	10	75		7		65	
PN4258	TO-92 (92)	12	12	4.5	10*	6	30	50	1	0.3	0.15	0.7	0.95	10	3	700	10	20		6		65	
PN4258A	TO-92 (92)	12	12	4.5	10*	6	30	50	1	0.5	0.5	1.5	50	10	3	700	10	18		6		65	
PN5140	TO-92 (92)	5	5	4	50*	3	20	40	1	0.5	0.2	1.2	10	50	5	400	10	20		6		65	
PN5910	TO-92 (92)	20	20	4.5	10*	10	30	50	1	0.3	0.15	0.75	0.95	10	3	700	10	20		6		65	
ST5771-1	TO-92 (92)	15	15	4.5	10	8	30	150	10	0.3	0.15	0.8	1	10		700	10					65	
ST5771-2	TO-92 (92)	15	15	4.5	10	8	35	50	1	0.5	0.18	0.8	0.95	10		700	10					65	
2N3244	TO-39	40	40	5	50	30	25	750	5	0.3	0.3	1.1	150	25	175	50	185		4			70	
2N3245	TO-39	50	50	5	50	50	20	1A	5	0.35	0.35	1.1	150	25	150	50	165		4			70	
2N3467	TO-39	40	40	5	100	30	40	120	500	1	0.3	1.0	150	25	175	50	90		4			70	

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D



SATURATED SWITCHES (Continued)

Type No.	Case Style	V <sub>CE0</sub> (V) Min	V <sub>BE0</sub> (V) Min	I <sub>CS</sub> * (nA) Max	I <sub>CB</sub> @ V <sub>CB</sub> (V)	h <sub>FE</sub>		I <sub>C</sub> & V <sub>CE</sub>		V <sub>CE(SAT)</sub> & V <sub>BE(SAT)</sub>		I <sub>C</sub> (mA)	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz)		I <sub>C</sub> (mA)	t <sub>off</sub> (ns) Max	NF (dB) Max	Test Conditions	Process No.
						Min	Max	I <sub>C</sub> (mA)	V <sub>CE</sub> (V)	Max	Min			Max	Min					
2N3468	TO-39	50	5	100	30	20	75	1	5	0.35	1.0	150	25	150	50	90		4	70	
NS3762	TO-39	40	5			30	120	1.5A	5	0.9	1.4	1A	18	180	50	115		10	70	
NS3763	TO-39	60	5			20	80	1.5A	5	0.9	1.4	1A	18	180	50	115		10	70	
2N5022	TO-39	50	5	100*	30	25	100	1	5	0.2	1.0	100	25	170	50	90		4	70	
2N5023	TO-39	30	5	100*	20	40	100	1	5	0.17	1.0	100	25	200	50	90		4	70	
DH3467CD	Ceramic DIP (40)	40	5	100	30	40	120	1	5	1.0	1.6	1A	25	175	50	90		4	70	
DH3467CN	Molded DIP (39)	40	5	100	30	40	120	1	5	1.0	1.6	1A	25	175	50	90		4	70	
DH3468CD	Ceramic DIP (40)	50	5	100	30	20	75	1	5	1.2	1.6	1A	25	150	50	90		4	70	
DH3468CN	Molded DIP (39)	50	5	100	30	20	75	1	5	1.2	1.6	1A	25	150	50	90		4	70	

T-37-01

TEST CONDITIONS:  
 (1) I<sub>C</sub> = 30 mA, V<sub>CC</sub> = 3V, I<sub>B</sub><sup>1</sup> = 3 mA, I<sub>B</sub><sup>2</sup> = 1.5 mA. (2) I<sub>C</sub> = 30 mA, V<sub>CC</sub> = 3V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 1.5 mA. (3) I<sub>C</sub> = 30 mA, V<sub>CC</sub> = 3V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 3 mA. (4) I<sub>C</sub> = 500 mA, V<sub>CC</sub> = 30V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 50 mA.  
 (5) I<sub>C</sub> = 10 mA, V<sub>CC</sub> = 3V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 1 mA. (6) I<sub>C</sub> = 10 mA, V<sub>CC</sub> = 1.5V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 1 mA. (7) I<sub>C</sub> = 10 mA, V<sub>CC</sub> = 1.5V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 500 μA. (8) I<sub>C</sub> = 10 mA, V<sub>CC</sub> = 2V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 1 mA. (9) I<sub>C</sub> = 50 mA, V<sub>CC</sub> = 3V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 5 mA. (10) I<sub>C</sub> = 1A, V<sub>CC</sub> = 30V, I<sub>B</sub><sup>1</sup> = I<sub>B</sub><sup>2</sup> = 100 mA.

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